4-bit dual supply translating transceiver; auto direction sensing

Rev. 1.0 — 10 December 2024

Product data sheet

1 General description

The P3A1604UK is a 4-bit, dual supply translating transceiver with auto direction sensing, that enables bidirectional voltage level translation. It features four 1-bit input-output ports (A and B), one output enable input (OE), and two supply pins (V_{CCA} and V_{CCB}). V_{CCA} can be supplied at any voltage between 0.72 V and 1.98 V. V_{CCB} can be supplied at any voltage between 1.62 V and 3.63 V. This flexibility makes the device suitable for translating between any of the voltage nodes (0.8 V, 1.2 V, 1.8 V, 2.5 V, and 3.3 V). Pins A and OE are referenced to V_{CCA} and pin B is referenced to V_{CCB}. A LOW level at pin OE causes the outputs to assume a high-impedance OFF-state.

2 Features and benefits

- · Auto direction sensing and bidirectional voltage level translation
- Wide supply voltage range:
- V_{CCA}: 0.72 V to 1.98 V and V_{CCB}: 1.62 V to 3.63 V
- No power-sequencing required
- Maximum data rate (DDR) per bit
 - Open-drain: 6.8 Mbit/s (3.4 MHz)
 - Push-pull: 40 Mbit/s (20 MHz)
- Support I3C/I2C/SMBus/SPI/UART interfaces
- Longer one-shot pulse for driving larger capacitive loads with much reduced ringing and overshoot
- A-side and OE inputs accept voltages up to 1.98 V
- · B-side inputs accept voltages up to 3.63 V
- Electrostatic discharge (ESD) protection:
 - Human body model (HBM) JESD22-A114E Class 2 exceeds 2000 V
 - Charged device model (CDM) JESD22-C101E exceeds 500 V
- I/O latch-up current 100 mA, JESD 78
- Package:
 - WLCSP12 (1.405 mm x 1.055 mm, 0.35 mm pitch)
- Specified from -40 °C to +125 °C

3 Applications

- Mobile
- I3C/I²C/SMBus
- SPI
- Server



4 Ordering information

Type number	Topside mark	Package					
		Name	Description	Version			
P3A1604UK	4U ^[1]		wafer level chip scale package; 12 balls with 0.35 mm pitch; 1.405 mm x 1.055 mm	SOT2063-4			

[1] "X4" for engineering sample and "4U" for production

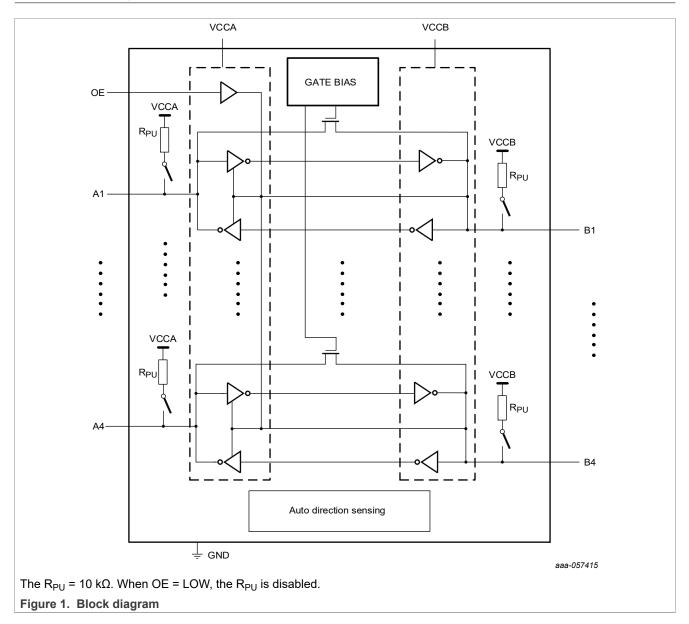
4.1 Ordering options

Table 2. Ordering options

	Orderable part number	Package	J	Minimum order quantity	Temperature
P3A1604UK	P3A1604UKAZ	WLCSP12	reel 7" q1/t1 *special mark chips dp	4400	T_{amb} = -40 °C to +125 °C

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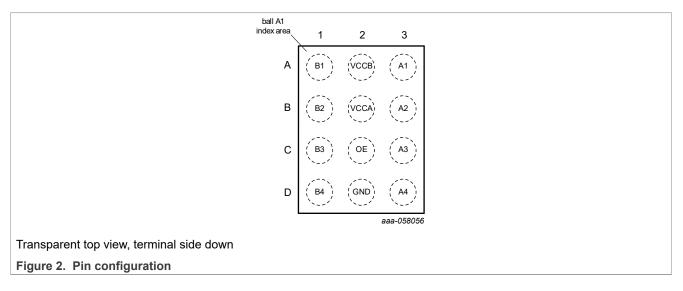
5 Block diagram



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6 Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
B1	A1	data input or output (referenced to V _{CCB})
V _{CCB}	A2	supply voltage B
A1	A3	data input or output (referenced to V _{CCA})
B2	B1	data input or output (referenced to V _{CCB})
V _{CCA}	B2	supply voltage A
A2	B3	data input or output (referenced to V _{CCA})
B3	C1	data input or output (referenced to V _{CCB})
OE	C2	output enable input (active High). Referenced to $V_{\mbox{\scriptsize CCA}}$
A3	C3	data input or output (referenced to V _{CCA})
B4	D1	data input or output (referenced to V _{CCB})
GND	D2	Ground
A4	D3	data input or output (referenced to V _{CCA})

7 Functional description

7.1 Architecture

The architecture of the device does not require an extra input signal to control the direction of data flow from A to B or B to A.

The P3A1604UK is a "switch" type voltage translator using two key circuits to enable voltage translation:

- 1. A pass-gate transistor (N-channel) that ties the ports together.
- 2. An output edge-rate one-shot accelerator that detects and accelerates rising and falling edges on the I/O pins.

Table 4 describes the function for different OE and I/O states.

Table 4.	Function	table
	i anotion	L'UNIO

Supply voltage		Input ^[1]	Input/output ^[1]	
V _{CCA}	V _{CCB}	OE	Α	В
0.72 V to 1.98 V and V _{CCA} ≤ V _{CCB}	1.62 V to 3.63 V	L	Z	Z
0.72 V to 1.98 V and V _{CCA} ≤ V _{CCB}	1.62 V to 3.63 V	Н	input or output	output or input
GND ^[2]	GND ^[2]	Х	Z	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

[2] When either V_{CCA} or V_{CCB} is at GND level, the device goes into Power-down mode.

7.2 Input driver requirements

As the P3A1604UK is a switch-type translator, properties of the input driver directly affect the output signal. The external open-drain or push-pull driver applied to an I/O determines the static current sinking capability of the system. The max data rate, HIGH-to-LOW output transition time (t_{THL}), and propagation delay (t_{PHL}), are dependent upon the output impedance and edge-rate of the external driver. The limits provided for these parameters in the data sheet assume a driver with an output impedance below 50 Ω is used.

7.3 Output load considerations

The maximum lumped capacitive load that can be driven is dependent upon the one-shot pulse duration. In cases with heavy capacitive loading, there is a risk that the output does not reach the positive rail within the one-shot pulse duration. The P3A1604UK has a longer one-shot pulse for driving larger capacitive loads.

To avoid excessive capacitive loading and to ensure correct triggering of the one-shot, use short trace lengths and low capacitance connectors on P3A1604UK PCB layouts. The length of the PCB trace should be such that the round-trip delay of any reflection is within the one-shot pulse duration (approximately 10 ns min to 30 ns max). It ensures low impedance termination and avoids output signal oscillations and one-shot retriggering.

If required, a series resistor on the signal path is recommended. See <u>Section 8.1</u> for more detail description.

7.4 Power up

During operation, V_{CCA} must never be higher than V_{CCB} . However, during power up, $V_{CCA} \ge V_{CCB}$ does not damage the device, so either power supply can be ramped up first.

It requires 50 μ s max after V_{CCB} reached regulating voltage and 4 μ s max after V_{CCA} reached regulating voltage for the internal circuit setup correctly.

There is no special power up sequencing required. The P3A1604UK includes circuitry that disables all output ports when either V_{CCA} or V_{CCB} is switched off.

7.5 Enable and disable

An output enable input (OE) is used to enable/disable the device. The OE is referenced to V_{CCA} . Setting OE = LOW causes all I/Os to assume the high-impedance OFF-state. The disable time (t_{dis} with no external load)

indicates the delay between when OE goes LOW and when outputs actually become disabled. The enable time (ten) indicates the amount of time the user must allow for one-shot circuitry to become operational after OE is taken HIGH. Before the ten (3 µs max), the I/O status should be ignored.

To ensure the high-impedance OFF-state during power up or power down, pin OE should be tied to GND through a pulldown resistor. The current-sourcing capability of the driver determines the minimum value of the resistor.

7.6 Pullup or pulldown resistors on I/O lines

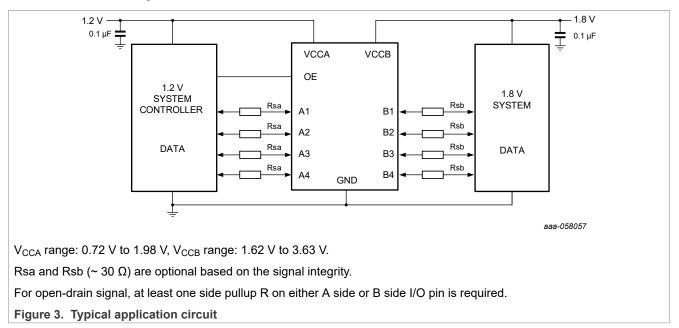
The A port I/O has an internal 10 k Ω pullup resistor to V_{CCA}. The B port I/O has an internal 10 k Ω pullup resistor to V_{CCB}. If a smaller value of pullup resistor is required, add an external resistor in parallel to the internal 10 k Ω . This pullup resistor affects the VOL level. When OE goes LOW, the internal pullups of the P3A1604UK are disabled. For Open Drain signal, at least one side pullup R on either A side or B side I/O pin is required. The pulldown resistor is not recommended to avoid incorrect I/O logic level.

8 Application information

8.1 Applications

P3A1604UK can be used in point-to-point applications to interface between devices or systems operating at different supply voltages. The device can support both open-drain and push-pull interfaces like I3C/I2C/SMBus/SPI/UART. See Figure 3 for the typical application circuit.

If the PCB trace length is too long (> 30 cm) or the parasitic impedance is too large, the I/O signal may have overshoot/undershoot or oscillation. A series resistor Rs on each I/O pin is recommended to reduce the overshoot/undershoot and avoid the oscillation. The recommended value is 30 Ω . Adjust the Rs value for optimized signal integrity is required based on with different wire lengths and PCB parasitic R/L/C. Ensure the Rs should not be too high to affect the VOL level.



8.2 Architecture

Figure 4 describes the architecture of P3A1604UK design for both push-pull and open drain mode. The architecture uses edge-rate accelerator circuitry (for both the high-to-low and low-to-high), N-channel Pass gate transistor and a pullup resistor (to provide DC-bias and drive capabilities) to meet these requirements. The design is directionless and does not need a direction control signal. The implementation supports both low-speed open-drain operation as well as high-speed push-pull operation. The N-channel Pass device T5 will be on only during the Low input cycle and will be off during the High input cycle.

When transmitting data from A-ports, during a rising edge and A port voltage = V_{IH} , both PMOS transistor T1 and T2 are turned on by OS1 (one-shot) and OS2 (one-shot) for a short duration respectively to reduce the low to high transition time. The T1 duration is around 10 ns. The T2 duration is around 10 ns min to 30 ns max, which depends on the CLB (load capacitance on the B side). Similarly, during a falling edge, when transmitting data from A to B and voltage = V_{IL} , both OS3 and OS4 one-shots turn on the N-channel transistor T3 and T4 for a short duration, which speeds up the high to low transition.

When transmitting data from B-ports, during a rising edge and B port voltage = V_{IH} , both PMOS transistor T1 and T2 are turned on by OS1 (one-shot) and OS2 (one-shot) for a short duration respectively to reduce the low to high transition time. The T2 duration is around 10 ns. The T1 duration is around 10 ns min to 30 ns max, which depends on the CLA (load capacitance on the A side). Similarly, during a falling edge, when transmitting data from B to A and voltage = V_{IL} , both OS3 and OS4 one-shots turn on the N-channel transistor T3 and T4 for a short duration, which speeds up the high to low transition.

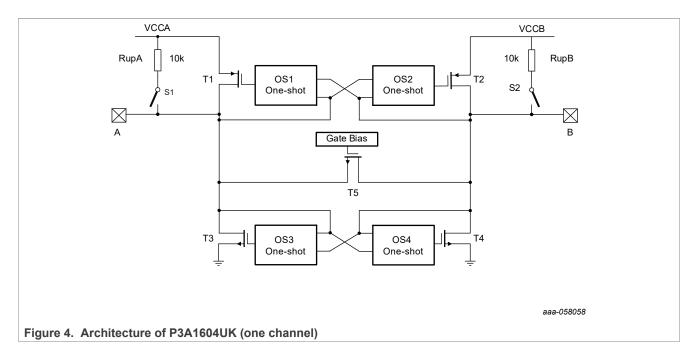
The internal pullup resistor RupA and RupB are typical value of 10 k and are controlled by switches S1 and S2 respectively. Switches S1 and S2 are controlled by their respective input signal and OE.

- Pullup resistors are connected only when the switches are closed.
 - The switches are closed only when the input signal is High and OE enabled.
- Pullup resistors are disconnected when the switches are open. Any one of the conditions have the switch open:
 - the respective input signal is low.
 - the OE input signal is low.

For push-pull application, the external pullup resistors are not required since at least one side is driven with a clear High or Low state.

For open-drain application, at least one external pullup resistor is required for pulling signal A from low state to high state. The external pullup resistor can be either on A side or B side. The rising time can be estimated with Rup_ext x (CLA + CLB) + one-shot time (~10 ns). Where the Rup_ext is an external pullup resistor, CLA is the total load capacitance on the A side. CLB is the total load capacitance on the B side.

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Limiting values 9

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

						-
Symbol	Parameter	Conditions		Min	Max	Unit
V _{CCA}	supply voltage A	$V_{CCA} \le V_{CCB}$	[1]	-0.5	+2.5	V
V _{CCB}	supply voltage B		[1]	-0.5	+4.2	V
VI	input voltage	A port and OE input		-0.5	+2.5	V
		B port		-0.5	+4.2	V
Vo	output voltage	Active mode				
		A or B port	[2] [3]	-0.5	V _{CCO} + 0.5	V
		Power-down or 3-state mode				
		A port		-0.5	+2.5	V
		B port		-0.5	+4.2	V
T _{stg}	storage temperature			-65	+150	°C

The minimum input and minimum output voltage ratings may be exceeded if the input and output current ratings are observed. [1]

[2] [3] V_{CCO} is the supply voltage associated with the output. V_{CCO} + 0.5 V should not exceed the associated V_{CCO} maximum limiting value.

Thermal characteristics 10

Table 6. Thermal resistance information^{[1][2]}

Symbol	Parameter	Value (type)	Unit
RθJA	Junction to ambient	77.9	°C/W
ΨJT	Junction to top characterization	9.3	°C/W

Determined in accordance to JEDEC JESD51-2A natural convection environment. Thermal resistance data in this report is solely for a thermal [1] performance comparison of one package to another in a standardized specified environment. It is not meant to predict the performance of a package in an application-specific environment

Recommended operating conditions 11

Table 7. Recommended operating conditions^[1]

Symbol	Parameter	Conditions		Min	Мах	Unit
V _{CCA}	supply voltage A	V _{CCA} ≤ V _{CCB} & 1.98 V	[2]	0.72	1.98	V
V _{CCB}	supply voltage B			1.62	3.63	V
VI_EN	OE input voltage			-0.3	V _{CCA} +0.3	V
T _{amb}	ambient temperature			-40	+125	°C
TJ	junction temperature		[3]	-40	+125	°C
Δt/ΔV	input transition rise and fall	A or B port; push-pull driving				
	rate	V _{CCA} = 0.72 V to 1.98 V; V _{CCB} = 1.62 V to 3.63 V	[2]	-	10	ns/V

The A and B sides of an unused I/O pair must be held in the same state, both at V_{CCI} or both at GND. [1]

 V_{CCA} must be less than or equal to $\dot{V_{CCB}}$ and 1.98 V. [2] [3]

The TJ limits shall be supported by proper thermal PCB design taking the power consumption and the thermal resistance into account.

12 Static characteristics

Table 8. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); T_{amb} = -40 °C to +125 °C, unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{IH} HIGH-level inpu voltage	HIGH-level input	A port					
	voltage	V _{CCA} = 0.72 V to 0.9 V; V _{CCB} = 1.62 V to 3.63 V		V _{CCA} – 0.2			V
		$V_{CCA} = 0.9 V \text{ to } 1.98 V;$ $V_{CCB} = 1.62 V \text{ to } 3.63 V;$ & $V_{CCA} \le V_{CCB}$		0.65 x V _{CCA}			V
		B port					
		$V_{CCA} = 0.72 \text{ V to } 1.98 \text{ V};$ $V_{CCB} = 1.62 \text{ V to } 3.63 \text{ V};$ & $V_{CCA} \le V_{CCB}$		0.65 x V _{CCB}			V
		OE input					
		$V_{CCA} = 0.72 \text{ V to } 1.98 \text{ V};$ $V_{CCB} = 1.62 \text{ V to } 3.63 \text{ V};$ & $V_{CCA} \le V_{CCB}$		0.65 x V _{CCA}			V
V _{IL}	LOW-level input voltage	A or B port					
		$V_{CCA} = 0.72 V \text{ to } 0.9 V;$ $V_{CCB} = 1.62 V \text{ to } 3.63 V;$	[1]	-		0.25 x V _{CCA}	V
		V _{CCA} = 0.9 V to 1.98 V;	[1]	-		0.35 x V _{CCA}	V

Thermal test board meets JEDEC specification for this package (JESD51-9). [2]

 Table 8. Static characteristics...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); $T_{amb} = -40$ °C to +125 °C, unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
		V_{CCB} = 1.62 V to 3.63 V; & $V_{CCA} \le V_{CCB}$					
		OE input					
		$V_{CCA} = 0.72 V \text{ to } 1.98 V;$ $V_{CCB} = 1.62 V \text{ to } 3.63 V;$ & $V_{CCA} \le V_{CCB}$		-		0.35 x V _{CCA}	V
/ _{OHA}	HIGH-level output	I _O = -10 μA					
	voltage	V_{CCB} = 1.62 V to 3.63 V; V _I ≥ 0.65 x V _{CCB}	[2]				
		V _{CCA} = 0.72 V to 0.9 V	[2]	0.70 x V _{CCA}		-	V
		$V_{CCA} = 0.9 V$ to 1.98 V; & $V_{CCA} \le V_{CCB}$	[2]	0.75 x V _{CCA}		-	V
/ _{ОНВ}	HIGH-level output	I _O = -10 μA					
	voltage	$V_{CCA} = 0.72 V \text{ to } 1.98 V;$ $V_{CCB} = 1.62 V \text{ to } 3.63 V;$ $V_I \ge 0.65 x V_{CCA}$	[2]	0.75 x V _{ССВ}		-	V
V _{OL}		A or B port; I _O = 1 mA	[2] [3]				
	voltage	V _I = 0.15 V; V _{CCA} = 0.72 V to 1.98 V; V _{CCB} = 1.62 V to 3.63 V		-		0.30	V
lı	input leakage current	OE; OE = 0 V or V _{CCA} ; V ₁ = 0 V or V _{CCI} ; V _{CCA} = 0.72 V to 1.98 V; V _{CCB} = 1.62 V to 3.63 V		-		1	μA
OZ	OFF-state output current	A or B port, OE = 0 V; V _{CCA} = 0.72 V to 1.98 V; V _{CCB} = 1.62 V to 3.63 V	[2]	-		2	μA
		$V_{CCA} = 0 V \text{ or } V_{CCB} = 0 V$				3	μA
сс	supply current	$\begin{array}{c} OE = V_{CCA}, V_{I} = 0 \; V \; or \; V_{CCI}; I_{O} = \\ 0 \; A \end{array}$	[4]				
		ICCA					
		V _{CCA} = 0.72 V to 1.98 V; V _{CCB} = 1.62 V to 3.63 V		-		5	μA
		V _{CCA} = 1.98 V; V _{CCB} = 0 V		-		5	μA
		V _{CCA} = 0 V; V _{CCB} = 3.63 V		-		-5	μA
		ICCB					
		V _{CCA} = 0.72 V to 1.98 V; V _{CCB} = 1.62 V to 3.63 V		-		15	μA
		V _{CCA} = 1.98 V; V _{CCB} = 0 V		-		-15	μA
		V _{CCA} = 0 V; V _{CCB} = 3.63 V		-		15	μA

Table 8. Static characteristics...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); Tamb = -40 °C to +125 °C, unless otherwise specified.

Symbol	Parameter	Conditions I		Min	Тур	Мах	Unit
		ICCA + ICCB					
		V _{CCA} = 0.72 V to 1.98 V; V _{CCB} = 1.62 V to 3.63 V		-		20	μA
CI	input capacitance	OE input; V_{CCA} = 1.2 V; V_{CCB} = 3.3 V		-	2	-	pF
C _{IO}	input/output capacitance	A port	[5]	-	7	-	pF
		B port	[5]	-	5.5	-	pF

[1] [2] [3]

 V_{IL} of A and B port is the value with respect to V_{CCA} . V_{CCO} is the supply voltage associated with the output. This spec has more margin. The Ron (resistance between input and output at low stage) max = 50 Ω . The equation for VOL is VOL= Vi + Io * Ron.

[4] [5] V_{CCI} is the supply voltage associated with the input The C_{IO} is defined when A port and B port are isolated.

Dynamic characteristics 13

Table 9. Dynamic characteristics for temperature range -40 °C to +125 °C^[1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7; for waveform see Figure 5 and Figure 6.

Symbol	Parameter	Conditions		V _{CCB}				Unit
				1.8 V ± 10 %		3.3 V ± 1	3.3 V ± 10 %	
				Min	Max	Min	Мах	
V _{CCA} = 0.8	3 V ± 10 %							
t _{PHL}	HIGH to LOW propagation delay	A to B			6		5	ns
t _{PLH}	LOW to HIGH propagation delay	A to B			8		7	ns
t _{PHL}	HIGH to LOW propagation delay	B to A			5		4	ns
t _{PLH}	LOW to HIGH propagation delay	B to A			2		2	ns
ten	enable time	OE to A; B			3		3	μs
t _{dis}	disable time	OE to A; no external load	[2]		0.4		0.4	μs
		OE to B; no external load	[2]		0.4		0.4	μs
		OE to A			0.8		0.8	μs
		OE to B			0.7		0.7	μs

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Symbol	Parameter	Conditions		V _{CCB}				Unit
				1.8 V ± 10 %		3.3 V ± 1	3.3 V ± 10 %	
				Min	Мах	Min	Мах	
t _{TLH}	LOW to HIGH output transition time	A port			3		3	ns
		B port			9		3	ns
t _{THL}	HIGH to LOW	A port			3		3	ns
	output transition time	B port			3		3	ns
t _{sk(o)}	output skew time	between channels			0.3		0.3	ns
t _W	pulse width	data inputs		25		25		ns
f _{data}	data rate	DDR	[3] [4]	0.128	40	0.128	40	Mbit/s
V _{CCA} = 1.2	2 V ± 10 %							
t _{PHL}	HIGH to LOW propagation delay	A to B			5		5	ns
t _{PLH}	LOW to HIGH propagation delay	A to B			5		5	ns
t _{PHL}	HIGH to LOW propagation delay	B to A			5		4	ns
t _{PLH}	LOW to HIGH propagation delay	B to A			2		2	ns
ten	enable time	OE to A; B			3		3	μs
t _{dis}	disable time	OE to A; no external load	[2]		0.4		0.4	μs
		OE to B; no external load	[2]		0.4		0.4	μs
		OE to A			0.8		0.8	μs
		OE to B			0.7		0.7	μs
t _{TLH}	LOW to HIGH	A port			6		4	ns
	output transition time	B port			6		3	ns
t _{THL}	HIGH to LOW	A port			3		3	ns
	output transition time	B port			3		3	ns
t _{sk(o)}	output skew time	between channels			0.3		0.3	ns
t _W	pulse width	data inputs		25		25		ns

Table 9. Dynamic characteristics for temperature range -40 °C to +125 °C^[1]...continued Voltages are referenced to GND (ground = 0 V); for test circuit see <u>Figure 7</u>; for waveform see <u>Figure 5</u> and <u>Figure 6</u>.

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Symbol	Parameter	Conditions		V _{CCB}			3.3 V ± 10 %	
				1.8 V ± 1	0 %	3.3 V ± 1		
				Min	Max	Min	Max	
f _{data}	data rate	DDR	[3] [4]	0.128	40	0.128	40	Mbit/s
V _{CCA} = 1.8	V ± 10 %							
t _{PHL}	HIGH to LOW propagation delay	A to B			5		5	ns
t _{PLH}	LOW to HIGH propagation delay	A to B			5		5	ns
t _{PHL}	HIGH to LOW propagation delay	B to A			5		4	ns
t _{PLH}	LOW to HIGH propagation delay	B to A			3		3	ns
ten	enable time	OE to A; B			3		3	μs
t _{dis}	disable time	OE to A; no external load	[2]		0.4		0.4	μs
		OE to B; no external load	[2]		0.4		0.4	μs
		OE to A			0.8		0.8	μs
		OE to B			0.7		0.7	μs
t _{TLH}	LOW to HIGH	A port			6		4	ns
	output transition time	B port			6		3	ns
t _{THL}	HIGH to LOW	A port			3		3	ns
	output transition time	B port			3		3	ns
t _{sk(o)}	output skew time				0.3		0.3	ns
t _W	pulse width	data inputs		25		25		ns
f _{data}	data rate	DDR	[3] [4]	0.128	40	0.128	40	Mbit/s

Table 9. Dynamic characteristics for temperature range -40 °C to +125 °C^[1]...continued Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7; for waveform see Figure 5 and Figure 6.

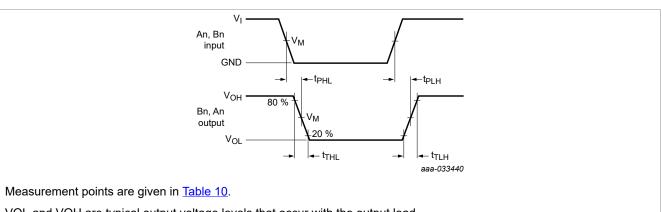
[1] [2]

 t_{en} is the same as t_{PZL} and t_{PZH} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} Delay between OE going LOW and when the outputs are disabled. Assuming CL (load capacitance) \leq 50 pF and equal time for 1 and 0 bit information. The one-shot accelerator duration (30 ns max) is proportional to CL and determined by the internal circuit. The spec is DDR (Double Data Rate) per bit. The 40 Mbit/s equivalents to 20 MHz. [3]

[4]

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14 Waveforms



VOL and VOH are typical output voltage levels that occur with the output load.

The data input (A, B) to data output (B, A) propagation delay times

Figure 5. The data input (A, B) to data output (B, A) propagation delay times

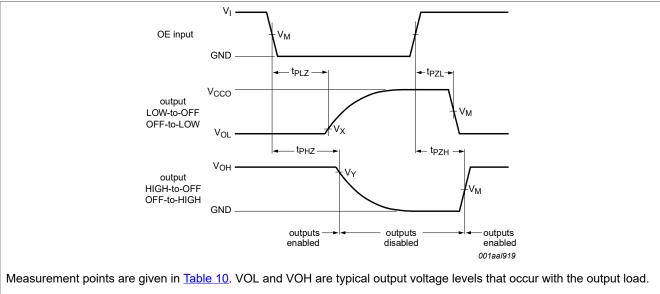


Figure 6. Enable and disable times

Table 10. Measurement points

V_{CCI} is the supply voltage associated with the input and VCCO is the supply voltage associated with the output.

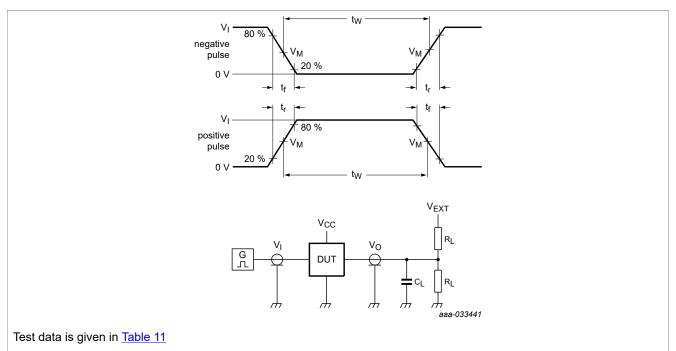
Supply Voltage	Input ^[1]	Output ^[2]					
V _{cco}	V _M	V _M	V _X	V _Y			
0.8 V ± 10 %	0.4 V _{CCI}	0.4 V _{CCO}	VOL + 0.08 V	VOH - 0.08 V			
1.2 V ± 10 %	0.4 V _{CCI}	0.4 V _{CCO}	VOL + 0.12 V	VOH - 0.12 V			
1.8 V ± 10 %	0.4 V _{CCI}	0.4 V _{CCO}	VOL + 0.18 V	VOH - 0.18 V			
3.3 V ± 10 %	0.4 V _{CCI}	0.4 V _{CCO}	VOL + 0.3 V	VOH - 0.3 V			

[2] V_{CCO} is the supply voltage associated with the output.

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All input pulses are supplied by generators having the following characteristics: PRR \leq 26 MHz; ZO = 50 Ω ; dV/dt \geq 1.0 V/ ns.

RL = Load resistance.

CL = Load capacitance including jig and probe capacitance.

VEXT = External voltage for measuring switching times.

Figure 7. Test circuit for measuring switching times

Supply Voltage	Input		Load		V _{EXT}			
V _{CCA}	V _{CCB}	V _I ^[1]	Δt/ΔV	CL ^[2]	RL ^[3]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ} ^[4]
0.72 V to 1.98 V; & ≤ V _{CCB}	1.62 V to 3.63 V	V _{CCI}	≤ 1.0 ns/V	50 pF	50 kΩ , 1 MΩ	open	open	2 V _{CCO}

[1] V_{CCI} is the supply voltage associated with the input.

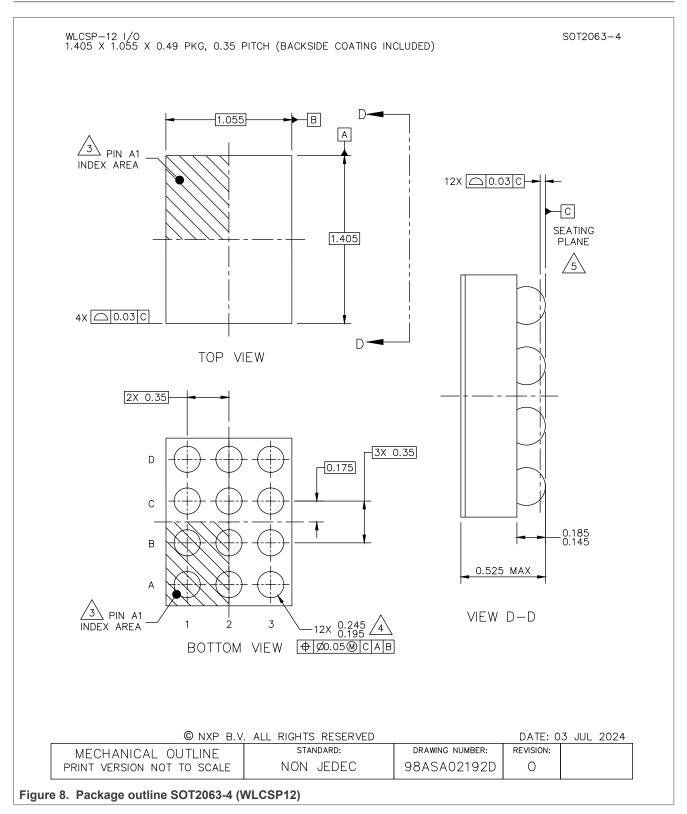
[2] For I3C maximum CL.

[3] For measuring data rate, pulse width, propagation delay and output rise and fall measurements, RL = 1 M Ω ; for measuring enable and disable times, RL = 50 k Ω .

[4] V_{CCO} is the supply voltage associated with the output.

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15 Package outline



Product data sheet

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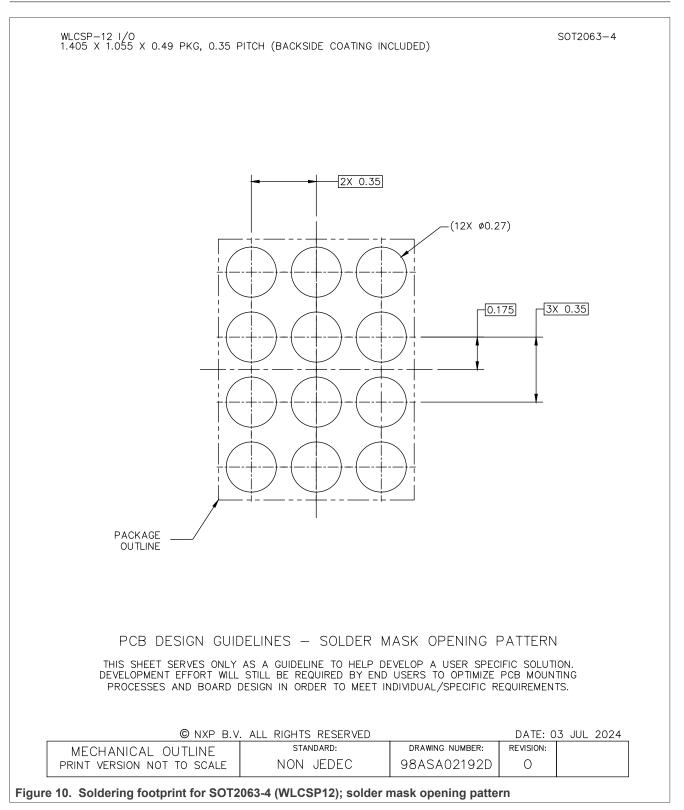
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WLCSI .405	^{12 I/O} х 1.055 х 0.49 РКG, 0.35 F	PITCH (BACKSIDE COATING IN	CLUDED)		SOT2063-4
NO	TES:				
1.	ALL DIMENSIONS IN MILLIMET	ERS.			
2.	DIMENSIONING AND TOLERAN)4.		
3.	PIN A1 FEATURE SHAPE, SIZ				
4	MAXIMUM SOLDER BALL DIA				
<u>/</u> 5.	DATUM C, THE SEATING PLA			OF THE SOL	DER BALLS
<u>/ 0. (</u> 6.	THIS PACKAGE HAS A BACK				
0.			51 0.020.		
	NXP B.V	. ALL RIGHTS RESERVED		DATE: C	3 JUL 2024
	CHANICAL OUTLINE	STANDARD:	DRAWING NUMBER:	REVISION:	
PRINT	VERSION NOT TO SCALE	NON JEDEC	98ASA02192D	0	

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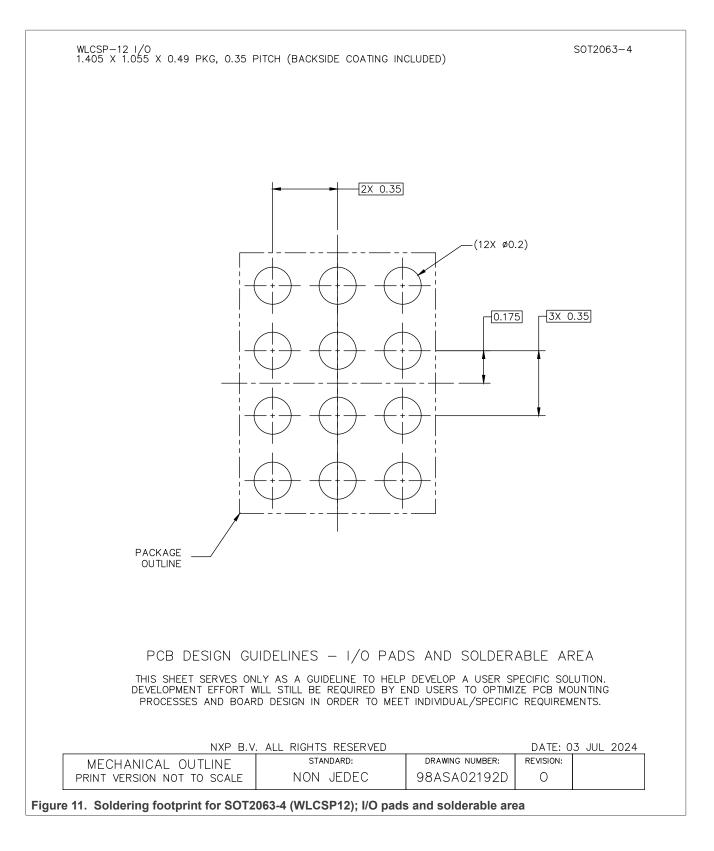
16 Soldering



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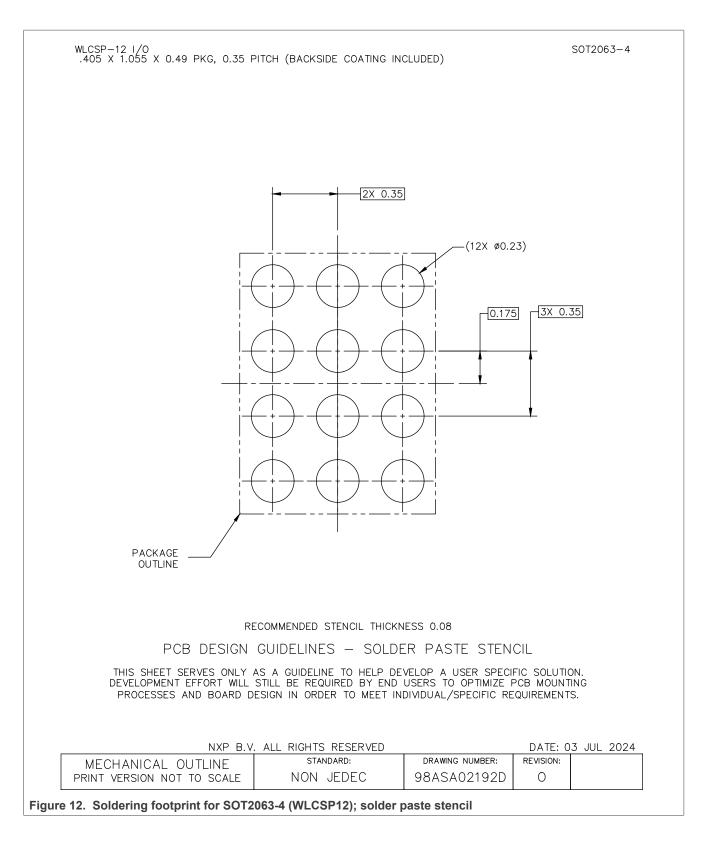


Product data sheet

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17 Revision history

Table 12. Revision history

Document ID	Release date	Description
P3A1604UK v.1.0	10 December 2024	Initial version

Legal information

Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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